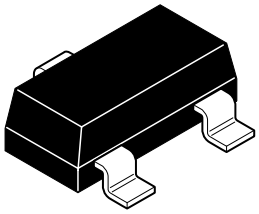
ZXTN25020DFH
20V SOT23 NPN medium power transistor

Summary



BV_{CEX} > 100V; $BV_{(BR)CEO}$ > 20V

BV_{ECO} > 5V;

$I_{C(CONT)}$ = 4.5A

$R_{CE(sat)}$ = 28 mΩ typical

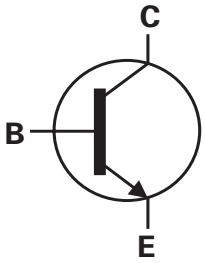
$V_{CE(sat)}$ < 43 mV @ 1A;

P_D = 1.25W

Complementary part number ZXTP25020DFH

Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

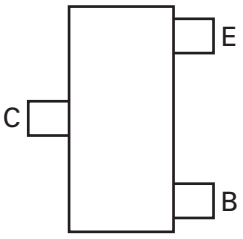


Features

- Higher power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 100V forward blocking voltage
- 5V reverse blocking voltage

Applications

- DC - DC converters
- MOSFET and IGBT gate driving
- LED driver
- Motor drive
- Relay, lamp and solenoid drive



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width	Quantity per reel
ZXTN25020DFHTA	7	8mm	3000

Device marking

016

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	100	V
Collector-emitter voltage (forward blocking)	V_{CEX}	100	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-collector voltage (reverse blocking)	V_{ECO}	5	V
Emitter-base voltage	V_{EBO}	7	V
Continuous collector current (c)	I_C	4.5	A
Base current	I_B	1	A
Peak pulse current	I_{CM}	15	A
Power dissipation at T_A =25°C (a)	P_D	0.73	W
Linear derating factor		5.84	mW/°C
Power dissipation at T_A =25°C (b)	P_D	1.05	W
Linear derating factor		8.4	mW/°C
Power dissipation at T_A =25°C (c)	P_D	1.25	W
Linear derating factor		9.6	mW/°C
Power dissipation at T_A =25°C (d)	P_D	1.81	W
Linear derating factor		14.5	mW/°C
Operating and storage temperature range	T_j, T_{stg}	- 55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient (a)	$R_{\Theta JA}$	171	°C/W
Junction to ambient (b)	$R_{\Theta JA}$	119	°C/W
Junction to ambient (c)	$R_{\Theta JA}$	100	°C/W
Junction to ambient (d)	$R_{\Theta JA}$	69	°C/W

NOTES:

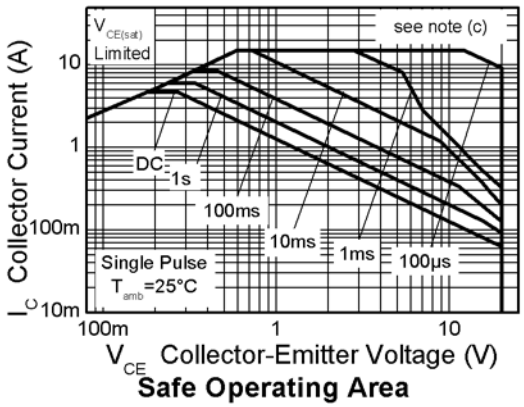
(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

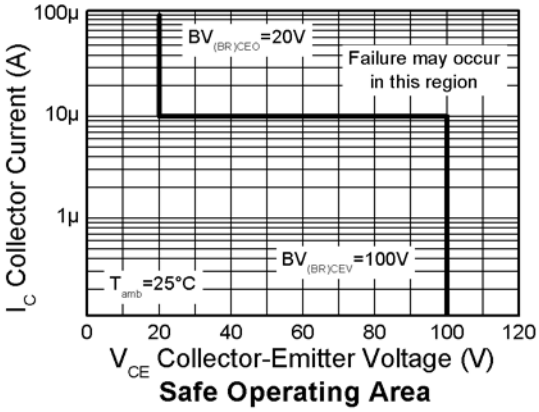
(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at t<5secs.

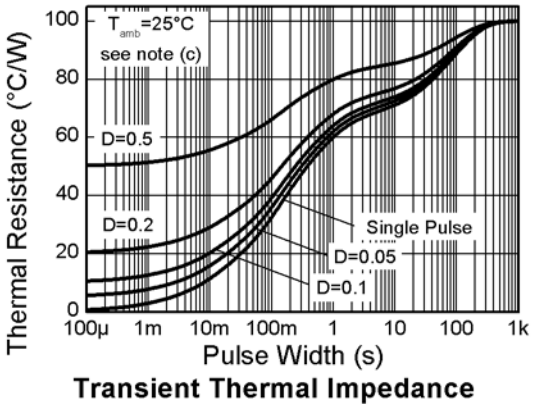
Characteristics



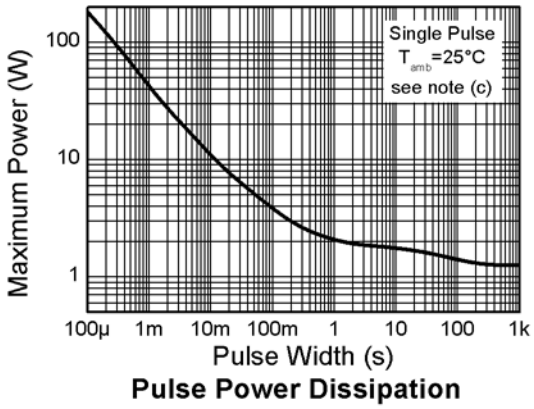
Safe Operating Area



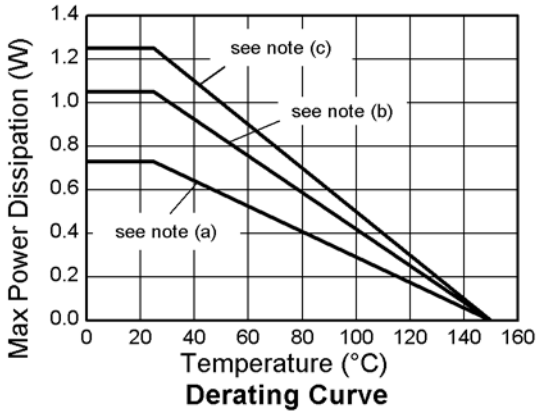
Safe Operating Area



Transient Thermal Impedance



Pulse Power Dissipation



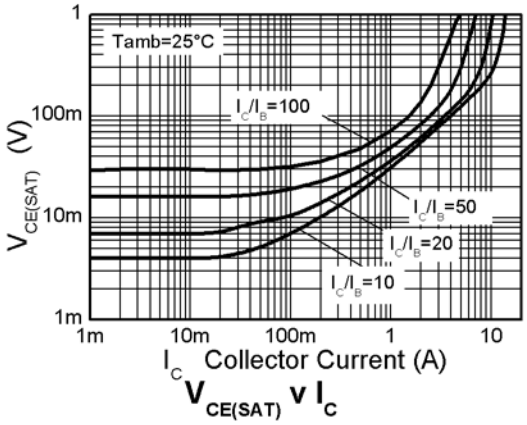
Derating Curve

Electrical characteristics (at T_{AMB} = 25°C unless otherwise stated)

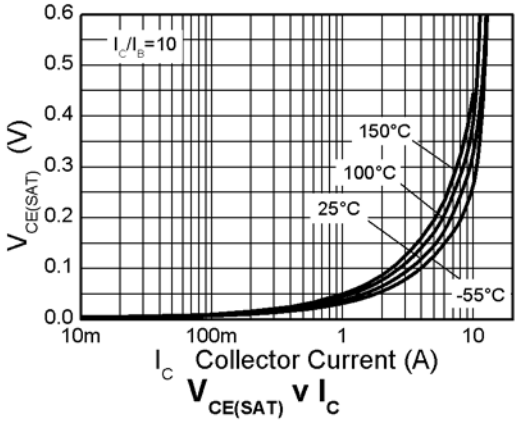
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector emitter breakdown voltage (base open)	BV_{CEO}	20	35		V	I_C = 10mA (*)
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECX}	6	8		V	I_E = 100μA, $R_{BC} \leq 1k\Omega$ or $0.25V > V_{BC} > -0.25V$
Emitter-collector breakdown voltage (base open)	BV_{ECO}	5	6		V	I_E = 100mA,
Emitter base breakdown voltage	BV_{EBO}	7	8.3		V	I_E = 100mA
Collector cut-off current	I_{CBO}		<1	50 20	nA μA	V_{CB} = 100V V_{CB} = 100V, T_{AMB}= 100°C
Collector emitter cut-off current	I_{CEX}		-	100	nA	V_{CE} = 100V; $R_{BE} \leq 1k\Omega$ or $-1V < V_{BE} < 0.25V$
Emitter cut-off current	I_{EBO}		<1	50	nA	V_{EB} = 5.6V
Collector emitter saturation voltage	$V_{CE(sat)}$		35	43	mV	I_C = 1A, I_B = 100mA(*)
			55	70	mV	I_C = 1A, I_B = 20mA(*)
			90	110	mV	I_C = 2A, I_B = 40mA(*)
			125	170	mV	I_C = 2A, I_B = 20mA(*)
			125	150	mV	I_C = 4,5A, I_B = 450mA (*)
			205	265	mV	I_C = 4.5A, I_B = 90mA(*)
Base emitter saturation voltage	$V_{BE(sat)}$		900	1000	mV	I_C = 4.5A, I_B = 90mA(*)
Base emitter turn-on voltage	$V_{BE(on)}$		820	900	mV	I_C = 4.5A, V_{CE} = 2V(*)
Static forward current transfer ratio	h_{FE}	300	450	900		I_C = 10mA, V_{CE} = 2V(*)
		250	380			I_C = 2A, V_{CE} = 2V(*)
		120	170			I_C = 4.5A, V_{CE} = 2V(*)
			15			I_C = 15A, V_{CE} = 2V(*)
Transition frequency	f_T		215		MHz	I_C = 50mA, V_{CE} = 10V f = 100MHz
Output capacitance	C_{OBO}		16.5	25	pF	V_{CB} = 10V, f = 1MHz(*)
Delay time	$t_{(d)}$		68		ns	V_{CC} = 10V. I_C = 1A, $I_{B1} = I_{B2}$= 10mA.
Rise time	$t_{(r)}$		72		ns	
Storage time	$t_{(s)}$		361		ns	
Fall time	$t_{(f)}$		64		ns	

NOTES:
(*) Measured under pulsed conditions. Pulse width ≤300μs; duty cycle ≤2%.

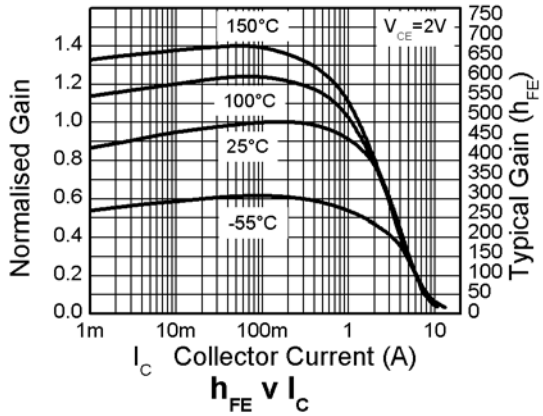
Characteristics



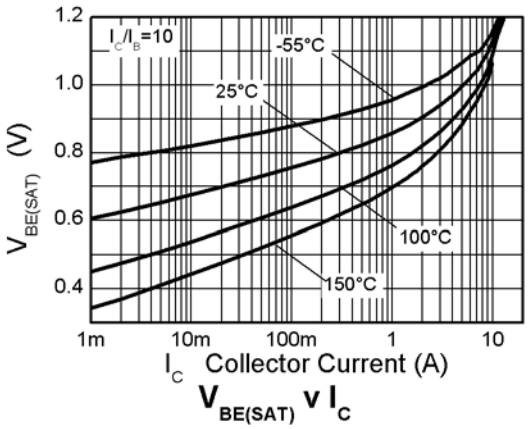
$V_{CE(SAT)}$ v I_C



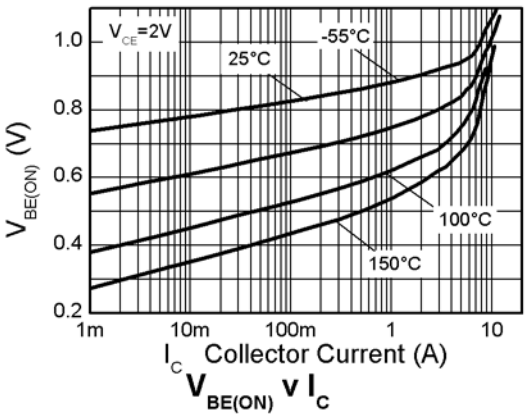
$V_{CE(SAT)}$ v I_C



h_{FE} v I_C

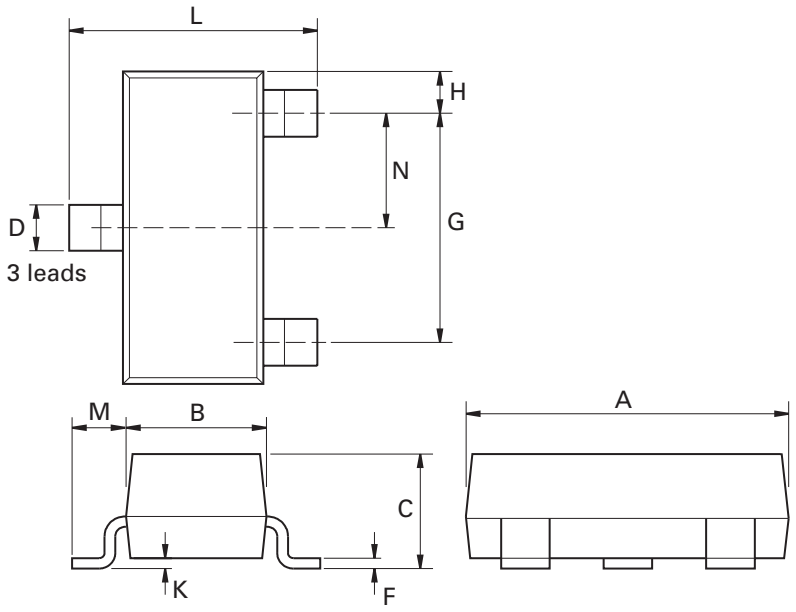


$V_{BE(SAT)}$ v I_C



$V_{BE(ON)}$ v I_C

Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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